

example alumina. The high temperature may include the temperature of a workpiece during a typical plasma etching process, i.e. about 300C. The shape of the support 306 may preferably include a conventional disk commonly used in plasma etching systems. The support 306 may be a conventional electrostatic chuck or may be a ceramic having a mechanical clamp for holding down the wafer 310. The thickness of the support 306 is preferably about 2mm. However any other thickness may be suitable. The support 306 construction may preferably be of a "thin disk bonded to a base" type, otherwise the lateral conduction may be so high that the heater input will be spread laterally resulting in an ineffective zone separation. The thickness of the support 306 may preferably be about 0.040". --

*cont'd  
A6*

Please amend the paragraph beginning at page 11, line 10 with the following paragraph:

*Q6*  
-- FIG. 3A illustrates a simplified schematic of the thermal dynamic in the apparatus of FIG. 3. The incoming flux Q1 contributes to the temperature T1 on the surface of the wafer 310. The heater 308 provides additional heat Q3 to the wafer 310. The flux Q2 exiting the system through the workpiece support 306 to the cooled base 302 is approximately equal to both incoming flux Q1 and Q3. Therefore: --

Please amend the paragraph beginning at page 13, line 22 with the following paragraph:

*A7*  
-- The first interface 506 and second interface 510 may comprise a layer of bonding adhesive, such as polymer. The thickness of each interface 506 and 510 may be preferably about .003". The thickness of the thermal insulator 508 and the workpiece holder 512 may be preferably about .040" each. --